74AUP1G07

Low-power buffer with open-drain output

Rev. 7 — 16 July 2012

Product data sheet

1. General description

The 74AUP1G07 provides the single non-inverting buffer with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ♦ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range Name		Description	Version					
74AUP1G07GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1					
74AUP1G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886					
74AUP1G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891					
74AUP1G07GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP1G07GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202					
74AUP1G07GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226					

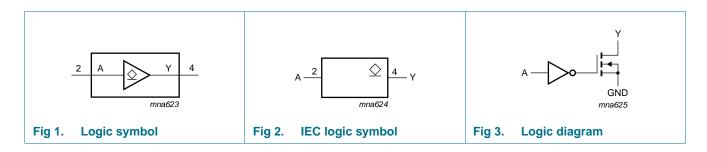
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1G07GW	pS
74AUP1G07GM	pS
74AUP1G07GF	pS
74AUP1G07GN	pS
74AUP1G07GS	pS
74AUP1G07GX	pS

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V_{CC}	5	6	supply voltage

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7. Functional description

Table 4. Function table[1]

Input	Output
Α	Υ
L	L
Н	Z

^[1] H = HIGH voltage level;

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage		<u>[1]</u> –0.5	+4.6	V
I_{OK}	output clamping current	V _O < 0 V	-50	-	mA
V_{O}	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	20	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
V_{I}	input voltage		0	3.6	V
V _O	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

L = LOW voltage level;

Z = high-impedance OFF state.

^[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

T _{amb} = 25	- 00					
	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	٧
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
l _{oz}	OFF-state output current	$V_I = V_{IH}$; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V; } V_{I} = \text{GND or } V_{CC}$	-	8.0	-	pF
Co	output capacitance	output enabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.7	-	рF
		output disabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.1	-	pF
Γ _{amb} = -4	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
	. ,	V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \ \mu A; \ V_{CC} = 0.8 \ V \ to \ 3.6 \ V$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I _I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$; $V_O = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC} = 0 \text{ V}$ to 3.6 V	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	$V_I = \text{GND or } V_{CC}; I_O = 0 \text{ A};$ V _{CC} = 0.8 V to 3.6 V		-	0.9	μΑ
∆l _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_0 = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
	40 °C to +125 °C HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}			V
V_{IH}	Therriever input voltage	$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.73 \times V_{CC}$ $0.70 \times V_{CC}$			V
		$V_{CC} = 0.3 \text{ V to } 1.33 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6			V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0		<u>-</u>	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-		0.25 × V _{CC}	
۷IL	LOVV-level illput voltage	$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$				
			-		0.30 × V _{CC}	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.7	V
\/	LOW lovel output voltage	••	-		0.9	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}			0.11	V
		$I_O = 20 \mu A; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$ $I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-		
			-	-	0.33 × V _{CC}	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
	lanut lankana arrasat	$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_1 = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μA
l _{OZ}	OFF-state output current	$V_1 = V_{1H}$; $V_O = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC} = 0 \text{ V}$ to 3.6 V	-	-	±0.75	μА
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ

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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

_ ...

Symbol	Parameter	Conditions		25 °C			-4	0 °C to +1	25 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 p$	F				•			•		
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	11.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.1	4.1	7.5	1.7	9.1	10.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.6	3.0	5.1	1.3	6.1	6.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.6	2.7	4.0	1.2	5.0	5.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.1	2.1	3.2	0.9	4.0	4.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.4	2.2	2.8	1.1	3.3	3.6	ns
C _L = 10	ρF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	14.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.0	5.1	9.0	2.4	11.2	12.3	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	3.8	6.1	2.0	7.4	8.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	3.6	4.8	1.8	6.1	6.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	2.8	3.8	1.3	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	3.1	4.2	1.6	4.5	5.0	ns
C _L = 15	ρF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	17.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.5	6.1	10.4	3.2	13.1	14.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	4.5	6.8	2.6	8.6	9.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.8	4.4	6.7	2.2	7.8	8.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.4	3.4	4.5	1.9	5.3	5.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	4.0	5.7	1.9	6.1	6.7	ns

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 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbo	Parameter	Conditions			25 °C		-4	0 °C to +1	125 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 30$	pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	24.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.8	9.0	15.6	4.3	18.8	20.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.1	6.7	9.4	3.7	11.8	13.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		3.8	6.8	9.7	3.2	11.0	12.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		3.7	5.2	6.7	3.0	7.1	7.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		3.6	6.4	9.7	2.8	10.4	11.4	ns
C _L = 5 p	oF, 10 pF, 15 pF and	30 pF								
C_{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	0.5	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	0.7	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	0.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	1.2	-	-	-	-	рF

^[1] All typical values are measured at nominal V_{CC} .

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

V_{CC} = supply voltage in V;

N = number of inputs switching.

^[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

^[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

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12. Waveforms

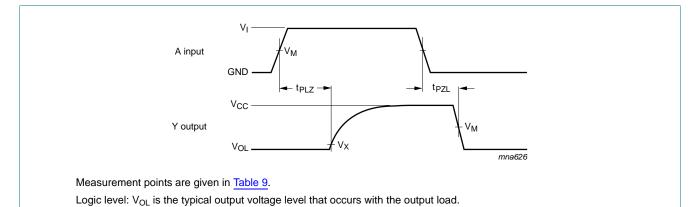
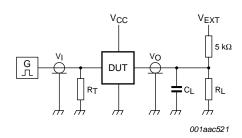


Fig 8. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output			
V _{CC}	V _M	V _M	V _X		
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.1 V		
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V		
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V		



Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Load circuitry for switching times

Table 10. Test data

Supply voltage	Load	Load			V _{EXT}			
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}			
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$			

^[1] For measuring enable and disable times, $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width, $R_L = 1 \text{ M}\Omega$.

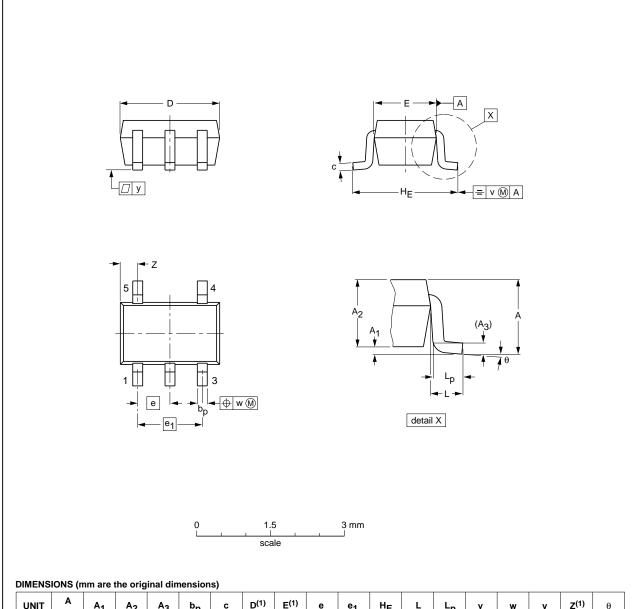
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13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION 153	ISSUE DATE
SOT353-1		MO-203	SC-88A			-00-09-01 03-02-19

Fig 10. Package outline SOT353-1 (TSSOP5)

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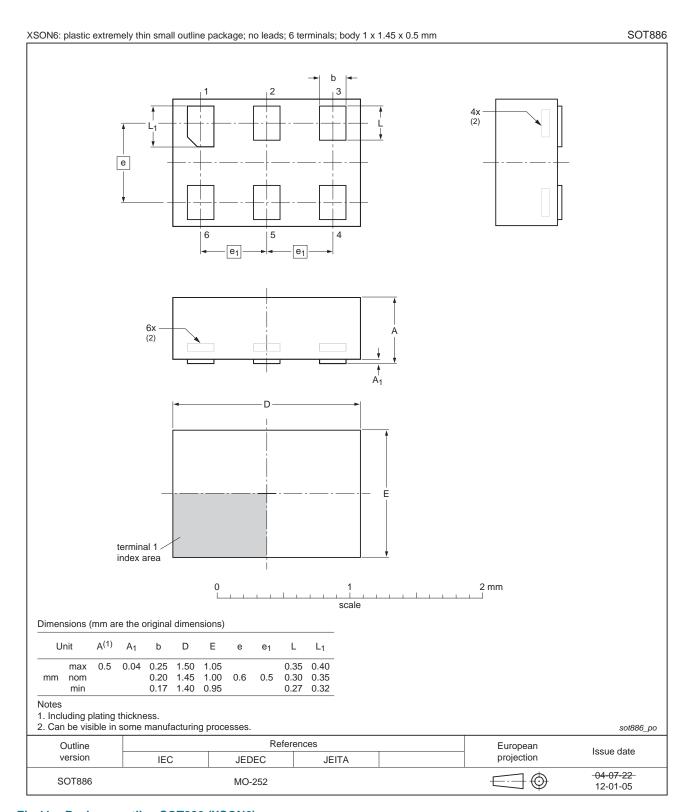


Fig 11. Package outline SOT886 (XSON6)

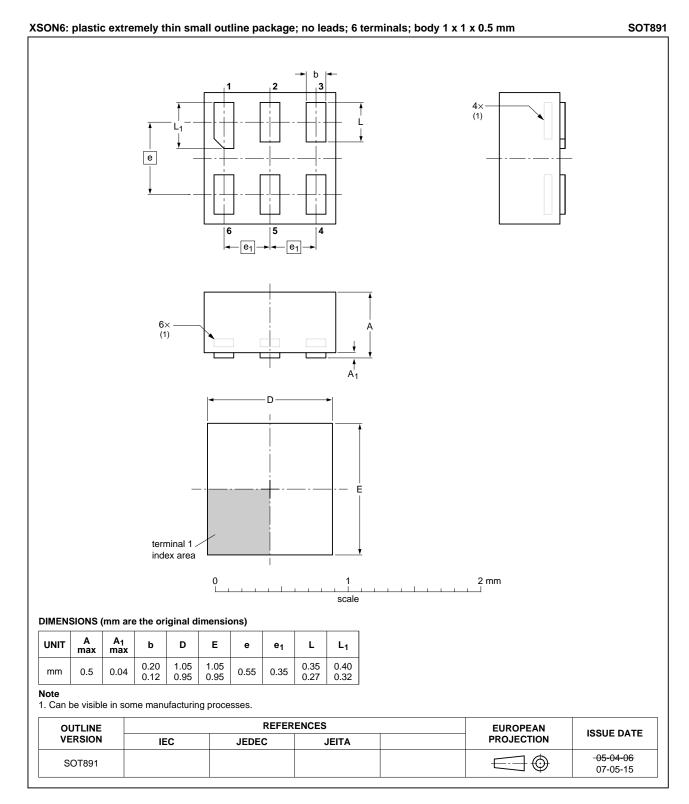


Fig 12. Package outline SOT891 (XSON6)

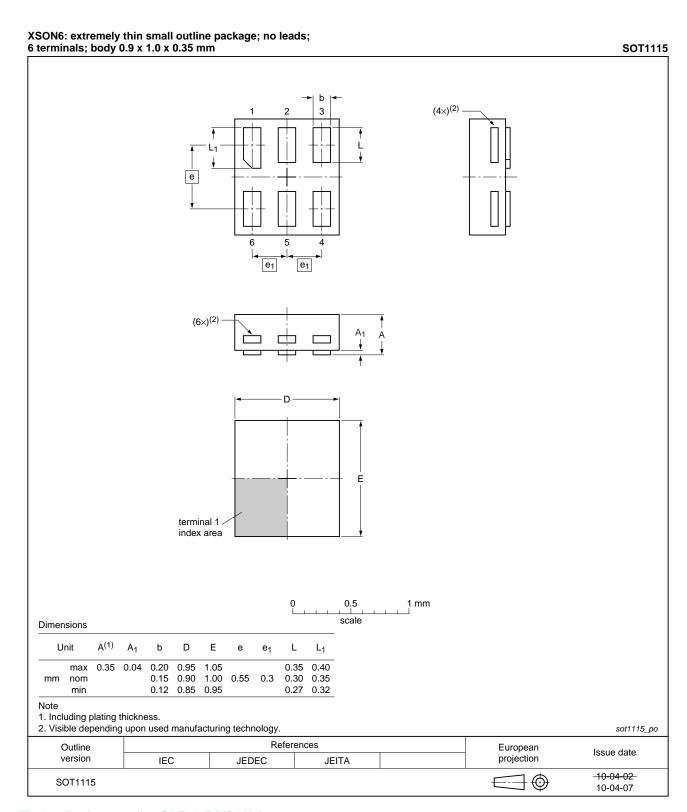


Fig 13. Package outline SOT1115 (XSON6)

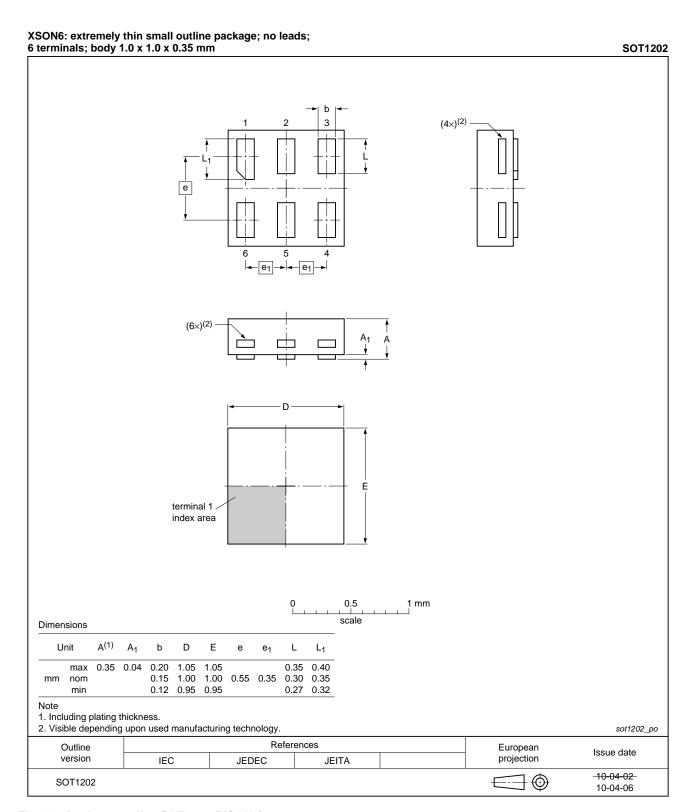


Fig 14. Package outline SOT1202 (XSON6)

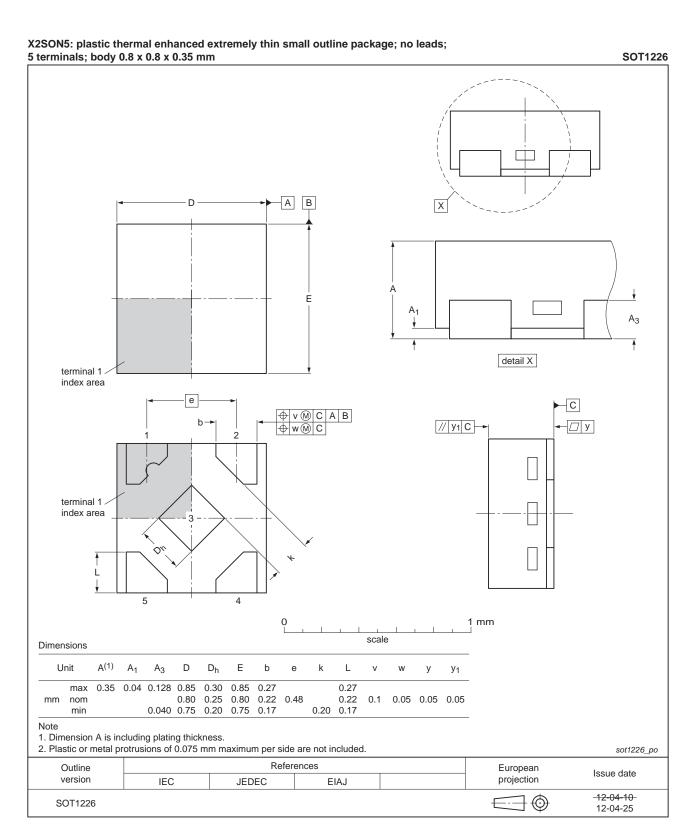


Fig 15. Package outline SOT1226 (X2SON5)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G07 v.7	20120716	Product data sheet	-	74AUP1G07 v.6
Modifications:	 Package ou 	tline drawing of SOT1226	(Figure 15) modified.	
74AUP1G07 v.6	20120412	Product data sheet	-	74AUP1G07 v.5
Modifications:	 Added type 	number 74AUP1G07GX (SOT1226)	
	 Package ou 	tline drawing of SOT886 (Figure 11) modified.	
74AUP1G07 v.5	20111115	Product data sheet	-	74AUP1G07 v.4
Modifications:	 Legal pages 	s updated.		
74AUP1G07 v.4	20100902	Product data sheet	-	74AUP1G07 v.3
74AUP1G07 v.3	20090617	Product data sheet	-	74AUP1G07 v.2
74AUP1G07 v.2	20070614	Product data sheet	-	74AUP1G07 v.1
74AUP1G07 v.1	20061010	Product data sheet	-	-

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16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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